Seat No.:	Enrolment No.

GUJARAT TECHNOLOGICAL UNIVERSITY

BE - SEMESTER-V (NEW) EXAMINATION - SUMMER 2021

	•	ect Code:3151105 Date:17/09	
	•	Name: VLSI Design	
		2:30 AM TO 01:00 PM Total Mar	ks: 70
Instr	uction	ns: Attempt all questions.	
	2. 3. 4.	Make suitable assumptions wherever necessary. Figures to the right indicate full marks. Simple and non-programmable scientific calculators are allowed.	
		Simple with their programment services outcomes and with their	MARKS
Q.1	(a) (b)	Describe: (1) Regularity (2) Modularity (3) Locality Differentiate Full Custom and Semi Custom Design flow	03 04
	(c)	Describe VLSI Design Flow.	07
Q.2	(a) (b)	Describe process of photo lithography with example. Describe FPGA Architecture.	03 04
	(c)	Sketch PMOS fabrication steps	07
	. ,	OR	
	(c)	Describe device isolation techniques with example.	07
Q.3	(a)	Derive equation for depletion depth for inversion region of two terminal MOS structure.	03
	(b)	Sketch Resistive load NMOS inverter circuit and its VTC. Derive equation of V_{OL}	04
	(c)	Describe Gradual Channel Approximation and Derive equation for drain current.	07
		OR	
Q.3	(a)	For NMOS transistor, gate voltage is 2v, drain voltage is 5v, source is connected to ground and threshold voltage is 1v. Find operating region of NMOS and drain current. (Kn = $60 \mu A/V^2$)	03
	(b)	Sketch CMOS inveter circuit and its VTC. Describe various regions of VTC. Derive equation for Vth.	04
	(c)	What is Scaling? Describe voltage scaling and derive necessary parameter.	07
Q.4	(a)	Define: τ_{PHL} , τ_{rise} with necessary diagram.	03
	(b)	Sketch and Describe D-Latch circuit using CMOS-Transmission Gate(TG).	04
	(c)	Why does NMOS pass strong logic-0 and weak logic-1? OR	07
Q.4	(a)	Describe CMOS ring oscillator	03
	(b)	Sketch static CMOS circuit for following Boolean equation. F1 = X'Y + XY' F2 = AB(C+D)	04
	(c)	Describe basic dynamic CMOS logic concept.	07
7.5	(a)	Describe FinEET Structure with neat diagram	03

	(b)	Describe Latch-up problem in IC.	04
	(c)	Describe different types of fault.	07
		OR	
Q.5	(a)	Compare FinFET and MOSFET.	03
	(b)	Describe methods for on-chip clock generation.	04
	(c)	Describe Ad-Hoc Testable design technique.	07
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